

Switching Diode

BAS16M3T5G

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

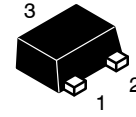
Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	100	Vdc
Peak Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

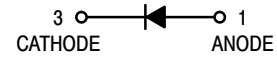
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR-4 Board (Note 1) $T_A = 25^\circ\text{C}$ Derated above 25°C	P_D	260	mW
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	490	$^\circ\text{C/W}$
Total Device Dissipation, FR-4 Board (Note 2) $T_A = 25^\circ\text{C}$ Derated above 25°C	P_D	580	mW
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	215	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

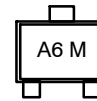
1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 Inch Pad



SOT-723
CASE 631AA
STYLE 2



MARKING DIAGRAM



A6 = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BAS16M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

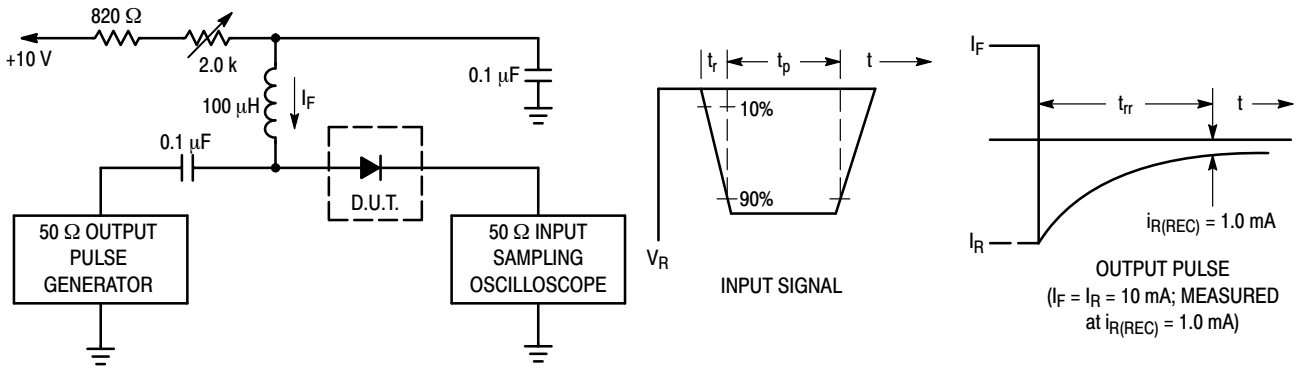
BAS16M3T5G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current ($V_R = 100\text{ Vdc}$) ($V_R = 75\text{ Vdc}$, $T_J = 150^\circ\text{C}$) ($V_R = 25\text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_R	- - -	1.0 50 30	$\mu\text{A dc}$
Reverse Breakdown Voltage ($I_{BR} = 100\ \mu\text{A dc}$)	$V_{(BR)}$	100	-	Vdc
Forward Voltage ($I_F = 1.0\ \text{mA dc}$) ($I_F = 10\ \text{mA dc}$) ($I_F = 50\ \text{mA dc}$) ($I_F = 150\ \text{mA dc}$)	V_F	- - - -	715 855 1000 1250	mV
Diode Capacitance ($V_R = 0$, $f = 1.0\ \text{MHz}$)	C_D	-	2.0	pF
Forward Recovery Voltage ($I_F = 10\ \text{mA dc}$, $t_r = 20\ \text{ns}$)	V_{FR}	-	1.75	Vdc
Reverse Recovery Time ($I_F = I_R = 10\ \text{mA dc}$, $R_L = 50\ \Omega$)	t_{rr}	-	6.0	ns
Stored Charge ($I_F = 10\ \text{mA dc}$ to $V_R = 5.0\ \text{Vdc}$, $R_L = 500\ \Omega$)	Q_S	-	45	pC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
 3. $t_p > t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

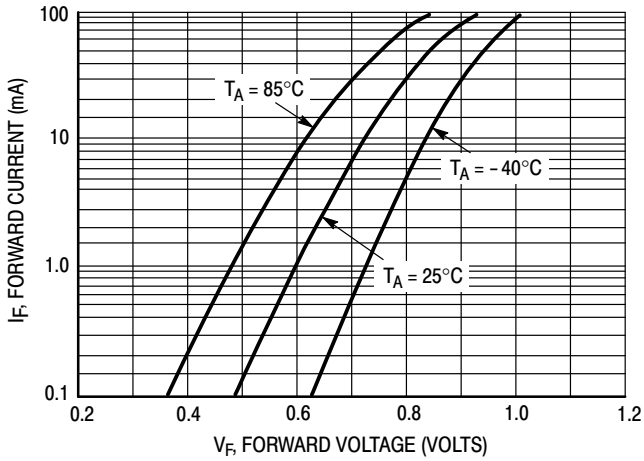


Figure 2. Forward Voltage

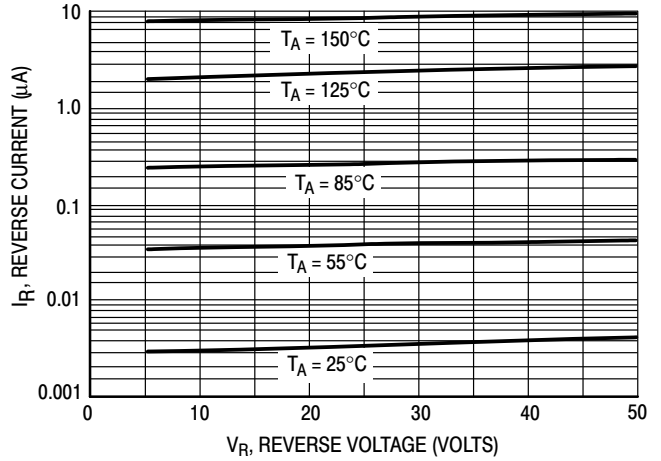


Figure 3. Leakage Current

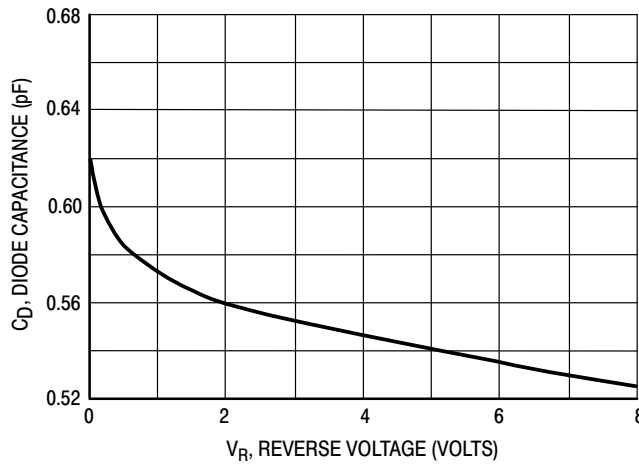


Figure 4. Capacitance

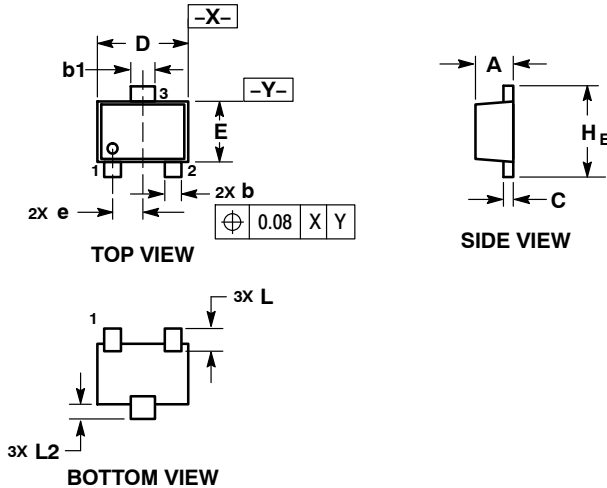
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 4:1

SOT-723
CASE 631AA
ISSUE D

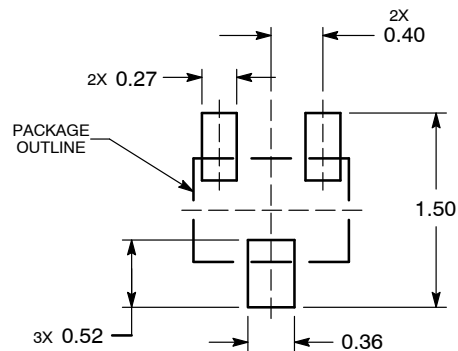
DATE 10 AUG 2009



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

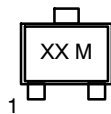
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- | | | | | |
|---|--|--|--|--|
| STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE | STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN |
|---|--|--|--|--|

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